

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S167	1	("6617681").PN.	USPAT; USOCR	OR	OFF	2007/09/18 11:19
S169	2	S168	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 12:00
S168	2	"20040104206"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 12:00
S90	2	"20040104206"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 12:00
S170	1	S169 and circuit with interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 12:01
S1	2419	semiconductor with interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:22
S172	1872	(semiconductor wafer) with (interposer dummy nonconduct\$5 non?conduct\$5 insulat\$5) near2 (aperture hole opening) with (circuit terminal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:26
S171	6023	(semiconductor wafer) with (interposer dummy nonconduct\$5 non?conduct\$5 insulat\$5) with (circuit terminal) with (aperture hole opening)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:26
S173	368	S172 and interpos\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:27
S174	68	S172 and interposer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:32

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S17 5	15	S172 and interposer with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:37
S18 5	0	S174 and interposer near3 window	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 14:59
S18 8	0	S171 and interposer near3 window	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:00
S18 7	0	S172 and interposer near3 window	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:00
S18 6	0	S173 and interposer near3 window	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:00
S19 1	0	interposer with (si?c\$1 sic\$1 sic (silicon adj carbide)) with coat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:09
S19 3	1	interposer same (si?c\$1 sic\$1 sic (silicon adj carbide)) with (coat\$4 layer\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:10
S19 2	0	interposer same (si?c\$1 sic\$1 sic (silicon adj carbide)) with coat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:10
S19 4	1005	circuit same (si?c\$1 sic\$1 sic (silicon adj carbide)) near3 (coat\$4 layer\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:11
S19 5	55	circuit with (si?c\$1 sic\$1 sic (silicon adj carbide)) near3 (coat\$4 layer\$4) with insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:12

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S19 7	28	interposer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:14
S19 8	28	interposer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:16
S20 0	2495	interlayer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:17
S19 9	530	interpos\$3 with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:17
S20 2	0	interlayer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon with window with contact not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:18
S20 1	2495	interlayer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon not S198 with window	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:18
S20 3	2	interlayer with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon with window not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:19
S20 5	30	dielectric with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon with window with (contact conduct\$4) not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:20
S20 4	65	dielectric with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon with window not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:20
S20 6	4	dielectric with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with silicon with window with (circuit) not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:26

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S20 7	0	dielectric with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 coat\$3 with silicon with window with (circuit) not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:27
S20 8	2	dielectric with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 coat\$3 with silicon with (window aperture opening hole) with (circuit) not S198	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:28
S20 9	155	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:29
S21 3	0	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon with (interl\$7 interp\$9 insulat\$5) with (circuit terminal contact tab connect\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:32
S21 2	0	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon with (interl\$7 interp\$9 insulat\$5) with (circuit terminal contact tab)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:32
S21 1	39	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon with (interl\$7 interp\$9 insulat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:32
S21 5	19	S211 not S214	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:37
S21 4	20	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon with (interl\$7 interp\$9 insulat\$5) with (circuit terminal contact tab connect\$4 electric\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:37
S21 6	568	S172 and (si?o\$1 sio\$1 sio (silicon adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:39
S19 6	864	circuit with (si?o\$1 sio\$1 sio (silicon adj oxide)) near3 (coat\$4 layer\$4) with insulat\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:39

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S21 0	45	(si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon same (interl\$7 interp\$9 insulat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:40
S21 7	0	S216 and (si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon same (interl\$7 interp\$9 insulat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 15:41
S21 8	0	S216 and (si?o\$1 sio\$1 sio (silicon adj oxide)) adj coat\$3 adj silicon same (interl\$7 interp\$9 insulat\$5 inbetween between)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/19 10:30
L1	1	("6221690").PN.	USPAT; USOCR	OR	OFF	2007/09/19 10:30
L4	0	1 and remov\$4 with resist same laser same encapsulat\$4 with mold\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/19 10:32
L3	0	1 and remov\$4 with resist with laser same encapsulat\$4 with mold\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/19 10:32
L5	1	1 and remov\$4 with resist with laser and remov\$4 with resist same encapsulat\$4 with mold\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/19 10:33
L2	1	1 and remov\$4 with resist same encapsulat\$4 with mold\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/19 10:33